

Fumihiro Matsukura

List of Publications by Year in Descending Order

Source: <https://exaly.com/author-pdf/8747501/fumihiro-matsukura-publications-by-year.pdf>

Version: 2024-04-27

This document has been generated based on the publications and citations recorded by exaly.com. For the latest version of this publication list, visit the link given above.

The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

92
papers

21,850
citations

41
h-index

92
g-index

92
ext. papers

23,427
ext. citations

6
avg, IF

6.53
L-index

#	Paper	IF	Citations
92	Electric-field effect on magnetic moments in Co ultra-thin films deposited on Pt. <i>Applied Physics Letters</i> , 2021 , 118, 152405	3.4	1
91	Magnetization dynamics and related phenomena in semiconductors with ferromagnetism. <i>Journal of Semiconductors</i> , 2019 , 40, 081502	2.3	
90	Electric-field effect on magnetic anisotropy in Pt/Co/Pd/MgO structures deposited on GaAs and Si substrates. <i>Applied Physics Express</i> , 2018 , 11, 013003	2.4	11
89	Temperature-dependent properties of CoFeB/MgO thin films: Experiments versus simulations. <i>Physical Review B</i> , 2018 , 98,	3.3	29
88	Damping constant in a free layer in nanoscale CoFeB/MgO magnetic tunnel junctions investigated by homodyne-detected ferromagnetic resonance. <i>Applied Physics Express</i> , 2017 , 10, 013001	2.4	7
87	Magnetic domain-wall creep driven by field and current in Ta/CoFeB/MgO. <i>AIP Advances</i> , 2017 , 7, 055918.5	1.5	5
86	Electric-field-induced magnetization switching in CoFeB/MgO magnetic tunnel junctions. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 0802A3	1.4	1
85	Annealing temperature dependence of magnetic properties of CoFeB/MgO stacks on different buffer layers. <i>Japanese Journal of Applied Physics</i> , 2017 , 56, 0802B2	1.4	11
84	Magnetization dynamics and its scattering mechanism in thin CoFeB films with interfacial anisotropy. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2017 , 114, 3815-3820	11.5	35
83	Magnetic-field-angle dependence of coercivity in CoFeB/MgO magnetic tunnel junctions with perpendicular easy axis. <i>Applied Physics Letters</i> , 2017 , 111, 132407	3.4	16
82	Electric-field effect on spin-wave resonance in a nanoscale CoFeB/MgO magnetic tunnel junction. <i>Applied Physics Letters</i> , 2017 , 111, 072403	3.4	14
81	Current-induced magnetization switching in a nano-scale CoFeB-MgO magnetic tunnel junction under in-plane magnetic field. <i>AIP Advances</i> , 2017 , 7, 055927	1.5	5
80	Temperature dependence of in-plane magnetic anisotropy and anisotropic magnetoresistance in (Ga,Mn)As codoped with Li. <i>Applied Physics Letters</i> , 2016 , 108, 112404	3.4	5
79	Adiabatic spin-transfer-torque-induced domain wall creep in a magnetic metal. <i>Nature Physics</i> , 2016 , 12, 333-336	16.2	32
78	Current-Induced Magnetization Switching of CoFeB/Ta/[Co/Pd (Pt)]-Multilayers in Magnetic Tunnel Junctions With Perpendicular Anisotropy. <i>IEEE Transactions on Magnetics</i> , 2016 , 52, 1-4	2	5
77	Magnetization Reversal by Field and Current Pulses in Elliptic CoFeB/MgO Tunnel Junctions With Perpendicular Easy Axis. <i>IEEE Magnetics Letters</i> , 2016 , 7, 1-4	1.6	11
76	Critical role of W deposition condition on spin-orbit torque induced magnetization switching in nanoscale W/CoFeB/MgO. <i>Applied Physics Letters</i> , 2016 , 109, 192405	3.4	53

75	Peculiar temperature dependence of electric-field effect on magnetic anisotropy in Co/Pd/MgO system. <i>Applied Physics Letters</i> , 2016 , 109, 082403	3-4	33
74	Effect of electric-field modulation of magnetic parameters on domain structure in MgO/CoFeB. <i>AIP Advances</i> , 2016 , 6, 075017	1-5	24
73	Electric-field-induced magnetization switching in CoFeB/MgO magnetic tunnel junctions with high junction resistance. <i>Applied Physics Letters</i> , 2016 , 108, 192406	3-4	58
72	Free- and reference-layer magnetization modes versus in-plane magnetic field in a magnetic tunnel junction with perpendicular magnetic easy axis. <i>Physical Review B</i> , 2016 , 94,	3-3	4
71	In-plane anisotropy of a nano-scaled magnetic tunnel junction with perpendicular magnetic easy axis. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 04DM03	1-4	4
70	Ferromagnetic resonance in nanoscale CoFeB/MgO magnetic tunnel junctions. <i>Journal of Applied Physics</i> , 2015 , 117, 17B708	2-5	13
69	Inverse spin Hall effect in Pt/(Ga,Mn)As. <i>Applied Physics Letters</i> , 2015 , 106, 222405	3-4	4
68	Spin-orbit torque induced magnetization switching in nano-scale Ta/CoFeB/MgO. <i>Applied Physics Letters</i> , 2015 , 107, 012401	3-4	131
67	Electric-field induced nonlinear ferromagnetic resonance in a CoFeB/MgO magnetic tunnel junction. <i>Applied Physics Letters</i> , 2015 , 107, 132404	3-4	12
66	Temperature dependence of energy barrier in CoFeB-MgO magnetic tunnel junctions with perpendicular easy axis. <i>Applied Physics Letters</i> , 2015 , 107, 152405	3-4	20
65	Control of magnetism by electric fields. <i>Nature Nanotechnology</i> , 2015 , 10, 209-20	28.7	571
64	CoFeB Thickness Dependence of Damping Constants for Single and Double CoFeB-MgO Interface Structures. <i>IEEE Magnetism Letters</i> , 2015 , 6, 1-3	1-6	27
63	Temperature dependence of lattice parameter of (Ga,Mn)As on GaAs substrate. <i>Japanese Journal of Applied Physics</i> , 2015 , 54, 098003	1-4	2
62	Magnetization reversal induced by in-plane current in Ta/CoFeB/MgO structures with perpendicular magnetic easy axis. <i>Journal of Applied Physics</i> , 2014 , 115, 17C714	2-5	28
61	Electric-field effects on magnetic anisotropy and damping constant in Ta/CoFeB/MgO investigated by ferromagnetic resonance. <i>Applied Physics Letters</i> , 2014 , 105, 052415	3-4	89
60	DC voltages in Py and Py/Pt under ferromagnetic resonance. <i>Applied Physics Express</i> , 2014 , 7, 013002	2-4	29
59	Magnetization switching in a CoFeB/MgO magnetic tunnel junction by combining spin-transfer torque and electric field-effect. <i>Applied Physics Letters</i> , 2014 , 104, 212406	3-4	72
58	Perpendicular-anisotropy CoFeB-MgO based magnetic tunnel junctions scaling down to 1X nm 2014 ,		18

57	Properties of (Ga,Mn)As codoped with Li. <i>Applied Physics Letters</i> , 2014 , 104, 222408	3-4	1
56	Properties of magnetic tunnel junctions with a MgO/CoFeB/Ta/CoFeB/MgO recording structure down to junction diameter of 11 nm. <i>Applied Physics Letters</i> , 2014 , 105, 062403	3-4	206
55	Electric field-induced ferromagnetic resonance in a CoFeB/MgO magnetic tunnel junction under dc bias voltages. <i>Applied Physics Letters</i> , 2014 , 105, 242409	3-4	35
54	In-plane magnetic field dependence of electric field-induced magnetization switching. <i>Applied Physics Letters</i> , 2013 , 103, 072408	3-4	41
53	MgO/CoFeB/Ta/CoFeB/MgO Recording Structure in Magnetic Tunnel Junctions With Perpendicular Easy Axis. <i>IEEE Transactions on Magnetics</i> , 2013 , 49, 4437-4440	2	97
52	Magnetotransport measurements of current induced effective fields in Ta/CoFeB/MgO. <i>Applied Physics Letters</i> , 2013 , 103, 262407	3-4	29
51	Three terminal magnetic tunnel junction utilizing the spin Hall effect of iridium-doped copper. <i>Applied Physics Letters</i> , 2013 , 102, 212408	3-4	85
50	Direct-current voltages in (Ga,Mn)As structures induced by ferromagnetic resonance. <i>Nature Communications</i> , 2013 , 4, 2055	17-4	75
49	Magnetic properties of MgO-[Co/Pt] multilayers with a CoFeB insertion layer. <i>Journal of Applied Physics</i> , 2013 , 113, 17C721	2-5	27
48	Size Dependence of Magnetic Properties of Nanoscale CoFeB/MgO Magnetic Tunnel Junctions with Perpendicular Magnetic Easy Axis Observed by Ferromagnetic Resonance. <i>Applied Physics Express</i> , 2013 , 6, 063002	2-4	34
47	Electric field-induced magnetization reversal in a perpendicular-anisotropy CoFeB-MgO magnetic tunnel junction. <i>Applied Physics Letters</i> , 2012 , 101, 122403	3-4	293
46	Observation of boron diffusion in an annealed Ta/CoFeB/MgO magnetic tunnel junction with standing-wave hard x-ray photoemission. <i>Applied Physics Letters</i> , 2012 , 101, 202402	3-4	56
45	Boron Composition Dependence of Magnetic Anisotropy and Tunnel Magnetoresistance in MgO/CoFe(B) Based Stack Structures. <i>IEEE Transactions on Magnetics</i> , 2012 , 48, 3829-3832	2	26
44	Perpendicular-anisotropy CoFeB-MgO magnetic tunnel junctions with a MgO/CoFeB/Ta/CoFeB/MgO recording structure. <i>Applied Physics Letters</i> , 2012 , 101, 022414	3-4	211
43	Magnetism of Co-doped ZnO epitaxially grown on a ZnO substrate. <i>Physical Review B</i> , 2012 , 85,	3-3	49
42	CoFeB Thickness Dependence of Thermal Stability Factor in CoFeB/MgO Perpendicular Magnetic Tunnel Junctions. <i>IEEE Magnetics Letters</i> , 2012 , 3, 3000204-3000204	1-6	81
41	Junction size effect on switching current and thermal stability in CoFeB/MgO perpendicular magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2011 , 99, 042501	3-4	123
40	Domain Structure in CoFeB Thin Films With Perpendicular Magnetic Anisotropy. <i>IEEE Magnetics Letters</i> , 2011 , 2, 3000304-3000304	1-6	100

39	Origin of the collapse of tunnel magnetoresistance at high annealing temperature in CoFeB/MgO perpendicular magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2011 , 99, 252507	3.4	50
38	Dependence of magnetic anisotropy on MgO thickness and buffer layer in Co ₂₀ Fe ₆₀ B ₂₀ -MgO structure. <i>Journal of Applied Physics</i> , 2011 , 109, 07C712	2.5	103
37	Tunnel magnetoresistance properties and annealing stability in perpendicular anisotropy MgO-based magnetic tunnel junctions with different stack structures. <i>Journal of Applied Physics</i> , 2011 , 109, 07C711	2.5	13
36	A perpendicular-anisotropy CoFeB-MgO magnetic tunnel junction. <i>Nature Materials</i> , 2010 , 9, 721-4	27	2491
35	Experimental probing of the interplay between ferromagnetism and localization in (Ga, Mn)As. <i>Nature Physics</i> , 2010 , 6, 22-25	16.2	190
34	Tunnel magnetoresistance properties and film structures of double MgO barrier magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2010 , 96, 192507	3.4	47
33	Domain wall creep in (Ga,Mn)As. <i>Applied Physics Letters</i> , 2010 , 97, 032504	3.4	13
32	Curie temperature versus hole concentration in field-effect structures of Ga _{1-x} Mn _x As. <i>Physical Review B</i> , 2010 , 81,	3.3	61
31	Electric double layer transistor with a (Ga,Mn)As channel. <i>Applied Physics Letters</i> , 2010 , 96, 022515	3.4	36
30	Electric-field effects on thickness dependent magnetic anisotropy of sputtered MgO/Co ₄₀ Fe ₄₀ B ₂₀ /Ta structures. <i>Applied Physics Letters</i> , 2010 , 96, 212503	3.4	383
29	Current induced effective magnetic field and magnetization reversal in uniaxial anisotropy (Ga,Mn)As. <i>Applied Physics Letters</i> , 2010 , 97, 222501	3.4	54
28	Simulation of magnetization switching by electric-field manipulation of magnetic anisotropy. <i>Applied Physics Letters</i> , 2010 , 96, 192506	3.4	40
27	MgO barrier-perpendicular magnetic tunnel junctions with CoFe/Pd multilayers and ferromagnetic insertion layers. <i>Applied Physics Letters</i> , 2009 , 95, 232516	3.4	124
26	ac susceptibility of (Ga,Mn)As probed by the anomalous Hall effect. <i>Journal of Applied Physics</i> , 2009 , 105, 07C516	2.5	
25	Magnetization vector manipulation by electric fields. <i>Nature</i> , 2008 , 455, 515-8	50.4	546
24	Chapter 5 Spintronic Properties of Ferromagnetic Semiconductors. <i>Semiconductors and Semimetals</i> , 2008 , 207-240	0.6	3
23	Tunnel magnetoresistance of 604% at 300K by suppression of Ta diffusion in CoFeB/MgO/CoFeB pseudo-spin-valves annealed at high temperature. <i>Applied Physics Letters</i> , 2008 , 93, 082508	3.4	1061
22	Properties of Ga _{1-x} Mn _x As with high x (>0.1). <i>Journal of Applied Physics</i> , 2008 , 103, 07D136	2.5	19

21	Electrical Curie temperature modulation in (Ga,Mn)As field-effect transistors with Mn composition from 0.027 to 0.200. <i>Journal of Applied Physics</i> , 2008 , 103, 07D139	2.5	6
20	2-Mb SPRAM design: bi-directional current write and parallelizing-direction current read based on spin-transfer torque switching. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 3929-3933	1.6	2
19	Channel Thickness Dependence of the Magnetic Properties in (Ga,Mn)As FET Structures. <i>Journal of Superconductivity and Novel Magnetism</i> , 2007 , 20, 409-411	1.5	3
18	Effect of electrode composition on the tunnel magnetoresistance of pseudo-spin-valve magnetic tunnel junction with a MgO tunnel barrier. <i>Applied Physics Letters</i> , 2007 , 90, 212507	3.4	270
17	Properties of Ga _{1-x} Mn _x As with high Mn composition (x>0.1). <i>Applied Physics Letters</i> , 2007 , 90, 122503	3.4	71
16	Tunnel magnetoresistance in MgO-barrier magnetic tunnel junctions with bcc-CoFe(B) and fcc-CoFe free layers. <i>Journal of Applied Physics</i> , 2006 , 99, 08A907	2.5	48
15	Giant tunnel magnetoresistance and high annealing stability in CoFeB/MgO/CoFeB magnetic tunnel junctions with synthetic pinned layer. <i>Applied Physics Letters</i> , 2006 , 89, 042506	3.4	137
14	Pulse-width and magnetic-field dependences of current-induced magnetization switching in a (Ga,Mn)As magnetic tunnel junction. <i>Journal of Applied Physics</i> , 2006 , 99, 08G514	2.5	7
13	Bias voltage dependence of the electron spin injection studied in a three-terminal device based on a (Ga,Mn)As _B -GaAs Esaki diode. <i>Applied Physics Letters</i> , 2006 , 89, 012103	3.4	35
12	Spin injection with three terminal device based on (Ga,Mn)As/n ⁺ -GaAs tunnel junction. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 4164-4167		5
11	Magnetic anisotropy in (Ga,Mn)As probed by magnetotransport measurements. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2006 , 3, 4086-4089		12
10	Effect of high annealing temperature on giant tunnel magnetoresistance ratio of CoFeB/MgO/CoFeB magnetic tunnel junctions. <i>Applied Physics Letters</i> , 2006 , 89, 232510	3.4	184
9	Effect of GaAs Intermediary Layer Thickness on the Properties of (Ga,Mn)As Tri-Layer Structures. <i>Journal of Superconductivity and Novel Magnetism</i> , 2006 , 18, 345-347		5
8	Dependence of Tunnel Magnetoresistance in MgO Based Magnetic Tunnel Junctions on Ar Pressure during MgO Sputtering. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, L1442-L1445	1.4	89
7	Magnetotransport properties of metallic (Ga,Mn)As films with compressive and tensile strain. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004 , 21, 1032-1036	3	111
6	Electrical manipulation of magnetization reversal in a ferromagnetic semiconductor. <i>Science</i> , 2003 , 301, 943-5	33.3	542
5	Hole-mediated ferromagnetism in tetrahedrally coordinated semiconductors. <i>Physical Review B</i> , 2001 , 63,	3.3	1333
4	Electric-field control of ferromagnetism. <i>Nature</i> , 2000 , 408, 944-6	50.4	1697

- | | | | |
|---|--|------|------|
| 3 | Zener model description of ferromagnetism in zinc-blende magnetic semiconductors. <i>Science</i> , 2000 , 287, 1019-22 | 33.3 | 6810 |
| 2 | Electrical spin injection in a ferromagnetic semiconductor heterostructure. <i>Nature</i> , 1999 , 402, 790-792 | 50.4 | 2126 |
| 1 | Epitaxy of (Ga, Mn)As, a new diluted magnetic semiconductor based on GaAs. <i>Journal of Crystal Growth</i> , 1997 , 175-176, 1069-1074 | 1.6 | 174 |